

Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable

$I_{F(AV)}$ 1380 A
 V_{RRM} 200~1000 V
 I_{FSM} 11 kA
 I^2t 605 $10^3 A^2S$



SYMBOL	CHARACTERISTIC	TEST CONDITIONS		$T_j(^{\circ}C)$	VALUE			UNIT
					Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled,	$T_C=85^{\circ}C$	190			1380	A
V_{RRM}	Repetitive peak reverse voltage	$t_p=10ms$		190	200		1000	V
I_{RRM}	Repetitive peak current	at V_{RRM}		190			30	mA
I_{FSM}	Surge forward current	10ms half sine wave		190			11	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$					605	$A^2s \cdot 10^3$
V_{FO}	Threshold voltage			190			0.87	V
r_F	Forward slope resistance						0.24	mΩ
V_{FM}	Peak forward voltage	$I_{FM}=1200A, F=7.0kN$		190			1.16	V
Q_{rr}	Recovery charge	$I_{FM}=1000A, t_p=1000\mu s, di/dt=-20A/\mu s, V_R=50V$		190		1600		μC
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 7.0kN					0.045	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.010	
F_m	Mounting force				5.3		10	kN
T_{stg}	Stored temperature				-40		190	$^{\circ}C$
W_t	Weight					80		g
Outline	P33							

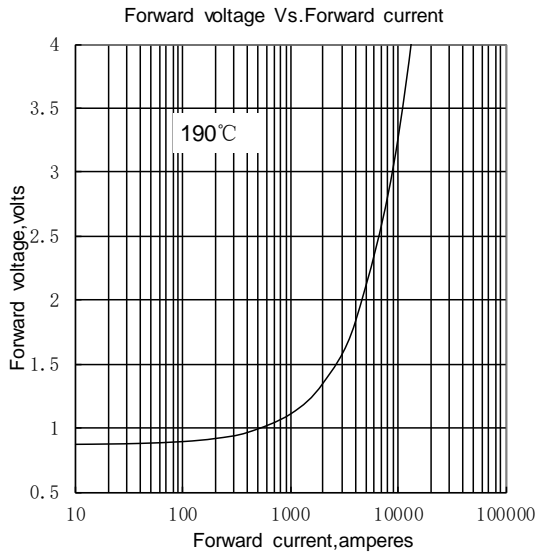


Fig.1

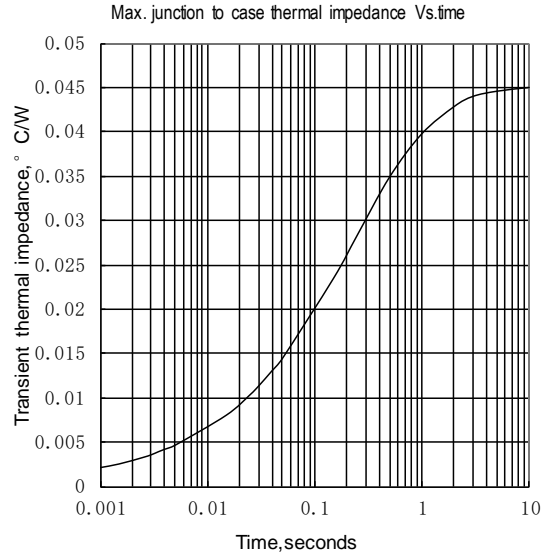


Fig.2

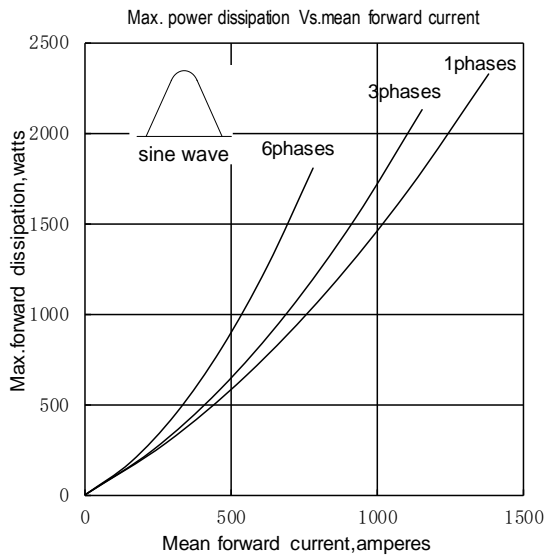


Fig.3

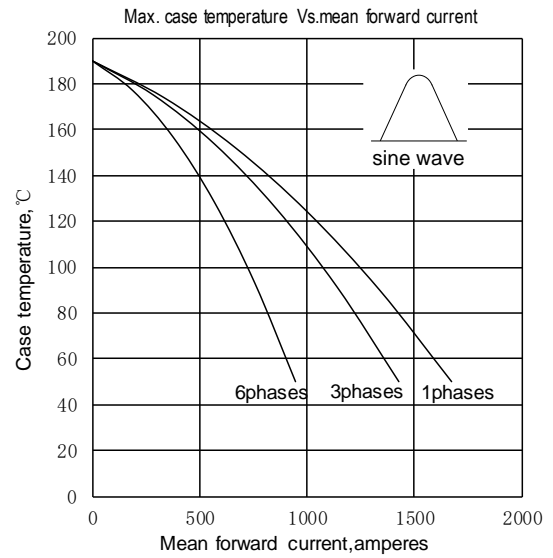


Fig.4

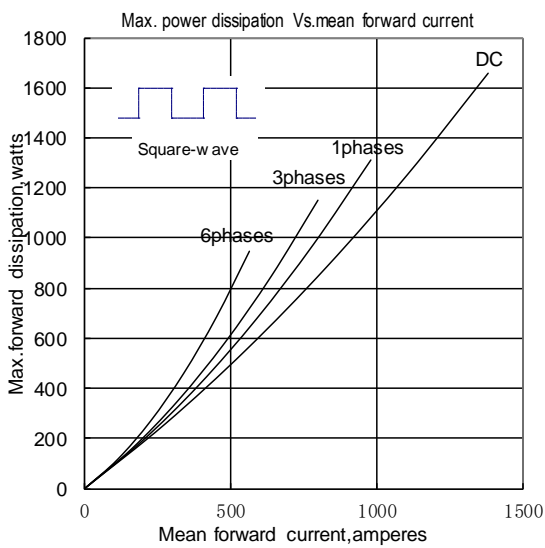


Fig.5

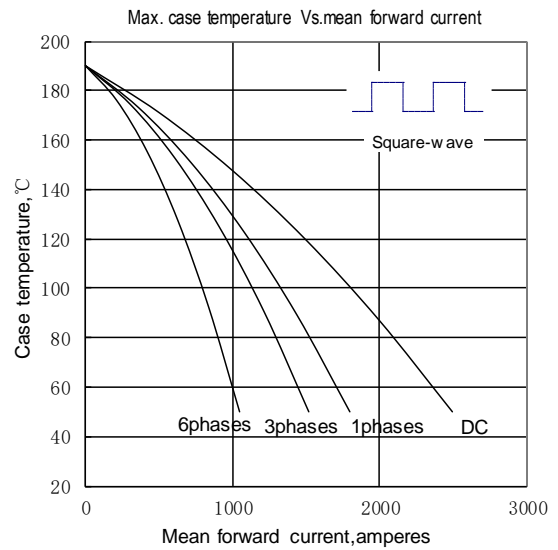


Fig.6

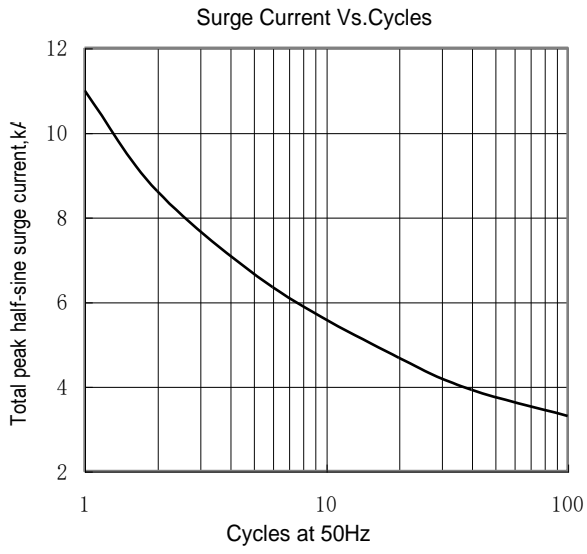


Fig.7

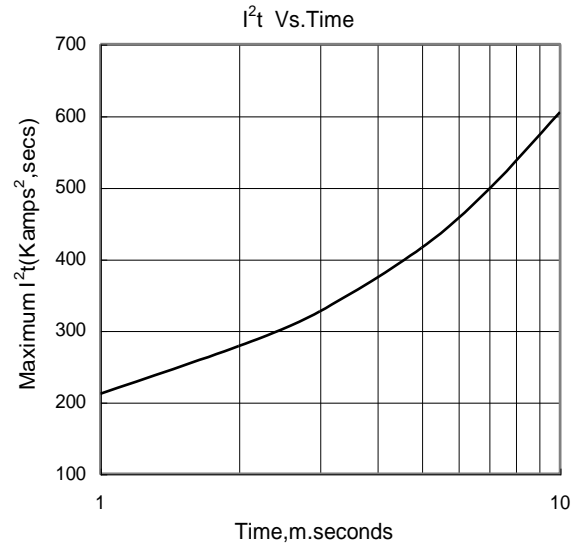


Fig.8

